3.3V ECL 1:2 Differential Fanout Buffer

Description

The MC100LVEL11 is a differential 1:2 fanout buffer. The device is functionally similar to the E111 device but with higher performance capabilities. Having within-device skews and output transition times significantly improved over the E111, the LVEL11 is ideally suited for those applications which require the ultimate in AC performance.

The differential inputs of the LVEL11 employ clamping circuitry to maintain stability under open input conditions. If the inputs are left open (pulled to V_{EE}) the Q outputs will go LOW.

Features

- 330 ps Propagation Delay
- 5 ps Skew Between Outputs
- High Bandwidth Output Transitions
- The 100 Series Contains Temperature Compensation
- PECL Mode Operating Range: $V_{CC} = 3.0$ V to 3.8 V with $V_{EE} = 0$ V
- NECL Mode Operating Range: $V_{CC} = 0 V$ with $V_{EE} = -3.0 V$ to -3.8 V
- Internal Input Pulldown Resistors on D, Pullup and Pulldown Resistors on D
- Q Output will Default LOW with Inputs Open or at $V_{\rm EE}$
- These Devices are Pb–Free and are RoHS Compliant

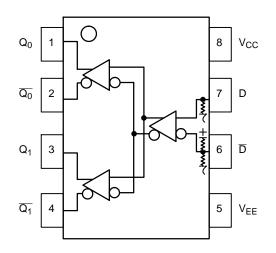
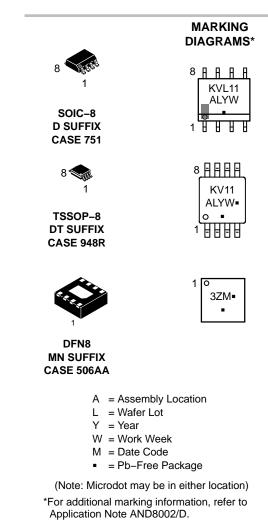


Figure 1. Logic Diagram and Pinout Assignment



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ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Table 1. PIN DESCRIPTION

Pin	Function
Q0, <u>Q0</u> ; Q1, <u>Q1</u>	ECL Data Outputs
D, D	ECL Data Inputs
V _{CC}	Positive Supply
V _{EE}	Negative Supply
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

Table 2. ATTRIBUTES

Character	Value					
Internal Input Pulldown Resistor	75 kΩ					
Internal Input Pullup Resistor	75 kΩ					
ESD Protection	Human Body Model Machine Model Charge Device Model	> 4 KV > 400 V > 2 kV				
Moisture Sensitivity, Indefinite Time	Level 1 Level 3 Level 1					
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in				
Transistor Count		63				
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test						

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Units
V _{CC}	PECL Mode Power Supply	$V_{EE} = 0 V$		8 to 0	V
V_{EE}	NECL Mode Power Supply	$V_{CC} = 0 V$		-8 to 0	V
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$\begin{array}{l} V_{I} \leq V_{CC} \\ V_{I} \geq V_{EE} \end{array}$	6 to 0 6 to 0	V
l _{out}	Output Current	Continuous Surge		50 100	mA mA
T _A	Operating Temperature Range			-40 to +95	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lpfm 500 lpfm	SOIC-8 SOIC-8	190 130	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8	41 to $44 \pm 5\%$	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lpfm 500 lpfm	TSSOP-8 TSSOP-8	185 140	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44 \pm 5%	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN8 DFN8	129 84	°C/W °C/W
T _{sol}	Wave Solder Pb-Free	<2 to 3 sec @ 260°C		265	°C
θ၂Ϲ	Thermal Resistance (Junction-to-Case)	(Note 2)	DFN8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 2. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

			−40°C			25°C			95°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current		24	28		24	28		25	30	mA
V _{OH}	Output HIGH Voltage (Note 4)	2215	2295	2420	2275	2345	2420	2275	2345	2420	mV
V _{OL}	Output LOW Voltage (Note 4)		1605	1745	1490	1595	1680	1490	1595	1680	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	2135		2420	2135		2420	2135		2420	mV
V _{IL}	Input LOW Voltage (Single–Ended)	1490		1825	1490		1825	1490		1825	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential) (Note 8) $V_{pp} < 500 \text{ mV}$ $V_{pp} \geqq 500 \text{ mV}$	1.2 1.4		3.1 3.1	1.1 1.3		3.1 3.1	1.1 1.3		3.1 3.1	V V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current D	0.5 -600			0.5 -600			0.5 -600			μΑ μΑ

Table 4. LVPECL DC CHARACTERISTICS V_{CC} = 3.3 V; V_{EE} = 0.0 V (Note 3)

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

3. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary ±0.3 V. 4. Outputs are terminated through a 50 Ω resistor to V_{CC} – 2.0 V.

V_{IHCMR} min varies 1:1 with V_{EE}, max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1.0 V.

Table 5. LVNECL DC CHARACTERISTICS $V_{CC} = 0.0 \text{ V}$; $V_{EE} = -3.3 \text{ V}$ (Note 6)

		-40°C		25°C			95°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current		24	28		24	28		25	30	mA
V _{OH}	Output HIGH Voltage (Note 7)	-1085	-1005	-880	-1025	-955	-880	-1025	-955	-880	mV
V _{OL}	Output LOW Voltage (Note 7)	-1830	-1695	-1555	-1810	-1705	-1620	-1810	-1705	-1620	mV
V _{IH}	Input HIGH Voltage (Single–Ended)	-1165		-880	-1165		-880	-1165		-880	mV
V _{IL}	Input LOW Voltage (Single–Ended)	-1810		-1475	-1810		-1475	-1810		-1475	mV
VIHCMR	Input HIGH Voltage Common Mode Range (Differential) (Note 8) $V_{pp} < 500 \text{ mV}$ $V_{pp} \ge 500 \text{ mV}$	-2.1 -1.9		-0.2 -0.2	-2.2 -2.0		-0.2 -0.2	-2.2 -2.0		-0.2 -0.2	V V
I _{IH}	Input HIGH Current			150			150			150	μΑ
IIL	Input LOW Current D	0.5 -600			0.5 -600			0.5 -600			μΑ μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

6. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary ± 0.3 V.

7. Outputs are terminated through a 50 Ω resistor to $V_{CC} - 2.0$ V. 8. V_{IHCMR} min varies 1:1 with V_{EE} , max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP} min and 1.0 V.

			−40°C		25°C			95°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Toggle Frequency					1.0					GHz
t _{PLH} t _{PHL}	Propagation Delay to Output	235		385	255	330	405	285		435	ps
t _{SKEW}	Within-Device Skew (Note 10) Device-to-Device (Note 11) Duty Cycle Skew (Note 12)		5 10	20 150 20		5 10	20 150 20		5 10	20 150 20	ps
t JITTER	Random Clock Jitter (RMS)					0.6					ps
V _{PP}	Input Swing (Note 13)	200		1000	200		1000	200		1000	mV
t _r t _f	Output Rise/Fall Times Q (20% – 80%)	120		320	120	220	320	120		320	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

9. V_{EE} can vary ± 0.3 V.

10. Within-device skew defined as identical transitions on similar paths through a device.

11. Device-to-device skew for identical transitions at identical V_{CC} levels.

Duty cycle skew is the difference between a t_{PLH} and t_{PHL} propagation delay through a device.
V_{PP}(min) is the minimum input swing for which AC parameters guaranteed. The device will function properly with input swings below 200 mV, however, AC delays may move outside of the specified range. The device has a DC gain of ≈40.

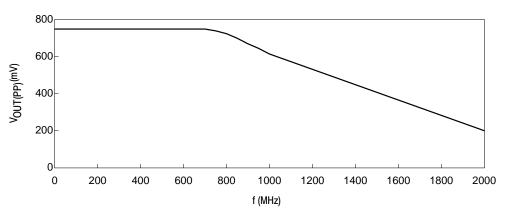


Figure 2. Output Swing versus Frequency

ORDERING INFORMATION

Device	Package	Shipping [†]
MC100LVEL11DG	SOIC–8 (Pb–Free)	98 Units / Rail
MC100LVEL11DR2G	SOIC–8 (Pb–Free)	2500 / Tape & Reel
MC100LVEL11DTG	TSSOP–8 (Pb–Free)	100 Units / Rail
MC100LVEL11DTR2G	TSSOP–8 (Pb–Free)	2500 / Tape & Reel
MC100LVEL11MNR4G	DFN8 (Pb–Free)	1000 / Tape & Reel

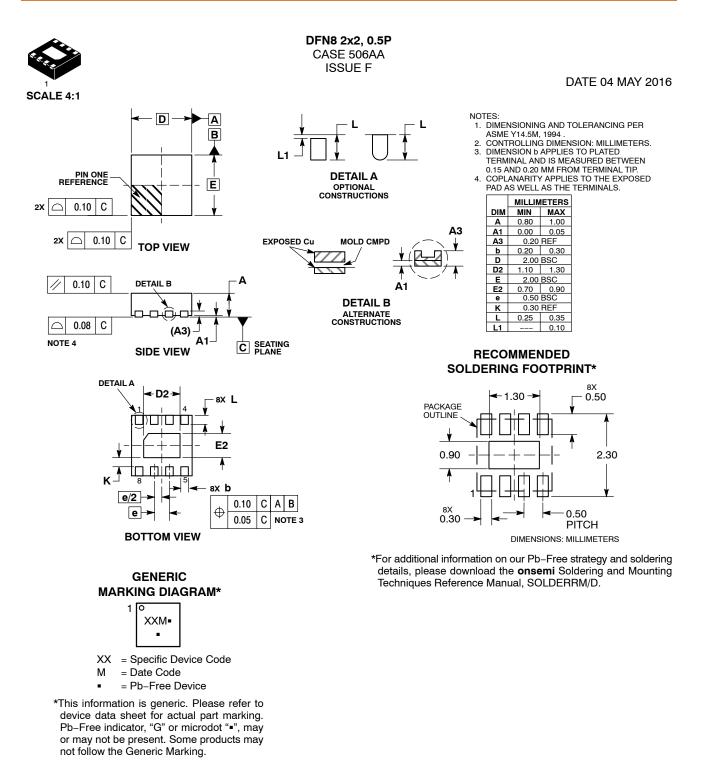
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

AN1405/D	_	ECL Clock Distribution Techniques
AN1406/D	_	Designing with PECL (ECL at +5.0 V)
AN1503/D	_	ECLinPS [™] I/O SPiCE Modeling Kit
AN1504/D	_	Metastability and the ECLinPS Family
AN1568/D	_	Interfacing Between LVDS and ECL
AN1672/D	_	The ECL Translator Guide
AND8001/D	_	Odd Number Counters Design
AND8002/D	_	Marking and Date Codes
AND8020/D	_	Termination of ECL Logic Devices
AND8066/D	_	Interfacing with ECLinPS
AND8090/D	_	AC Characteristics of ECL Devices

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

6.

7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

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STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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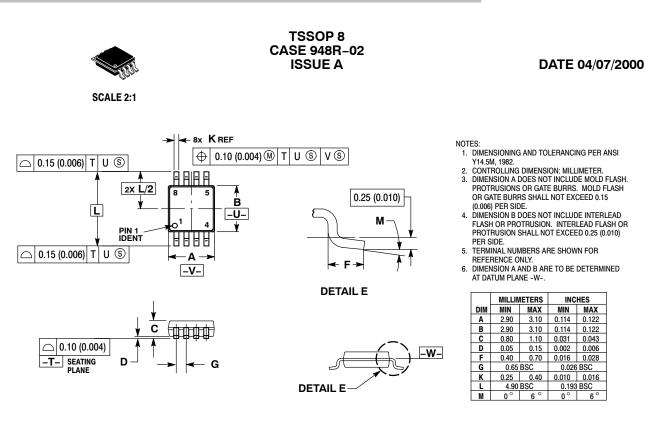
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